

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Tomohiko SHIBATA, Yukinori NAKAMURA and Mitsuhiro TANAKA

Filed: Concurrently Herewith

For: A SUBSTRATE USABLE FOR AN ACOUSTIC SURFACE WAVE DEVICE, A
METHOD FOR FABRICATING THE SAME SUBSTRATE AND AN ACOUSTIC
SURFACE WAVE DEVICE HAVING THE SAME SUBSTRATE

Box Patent Application
Assistant Commissioner for Patents
Washington DC 20231

PRELIMINARY AMENDMENT

Sir:

Prior to examination, Applicants wish to amend the subject application as follows:

In the Claims:

Please rewrite claim 5 as follows:

5. (Amended) A fabricating method as defined in claim 3, wherein the forming pressure of the AlN film is set within a range of 7-17 Torr.

I hereby certify that this paper is being deposited with the United States Postal Service
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Elizabeth A. VanAntwerp

REMARKS

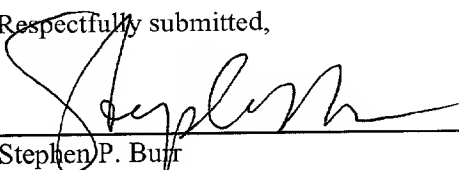
Claims 1-7 are pending herein. Applicants have amended claim 5 to eliminate multiple dependency. No new matter has been added. Applicants believe the case is now in condition for examination.

Attached hereto as page3 is a marked-up version of the changes made to claim 5 by the current Amendment. The attached page is captioned "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

If the Examiner believes that contact with applicants' attorney would be advantageous toward the disposition of this case, he is herein requested to call applicants' attorney at the phone number noted below.

November 30, 2001
Date

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

Claim 5 has been amended as follows:

5. (Amended) A fabricating method as defined in claim 3 ~~or 4~~, wherein the forming pressure ✓
of the AlN film is set within a range of 7-17 Torr.